

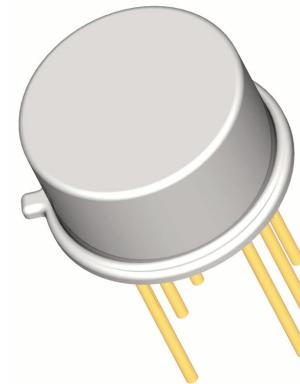
**Description**

Semicoa Semiconductors offers:

- Screening and processing per MIL-PRF-19500 Appendix E
- JAN level (2N3810J)
- JANTX level (2N3810JX)
- JANTXV level (2N3810JV)
- JANS level (2N3810JS)
- QCI to the applicable level
- 100% die visual inspection per MIL-STD-750 method 2072 for JANTXV and JANS
- Radiation testing (total dose) upon request

**Applications**

- General purpose
- Matched Dual transistors
- PNP silicon transistor

**Features**

- Hermetically sealed TO-78 metal can
- Also available in chip configuration
- Chip geometry 0220
- Reference document: MIL-PRF-19500/336

**Benefits**

- Qualification Levels: JAN, JANTX, JANTXV and JANS
- Radiation testing available

**Absolute Maximum Ratings**

$T_c = 25^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CEO}$	60	Volts
Collector-Base Voltage	$V_{CBO}$	60	Volts
Emitter-Base Voltage	$V_{EBO}$	5	Volts
Collector Current, Continuous	$I_C$	50	mA
Power Dissipation, $T_A = 25^\circ\text{C}$ Derate linearly above $25^\circ\text{C}$	$P_T$	300 one section 600 both sections 1.71 one section 3.43 both sections	mW $\text{mW}/^\circ\text{C}$
Operating Junction Temperature	$T_J$	-65 to +200	°C
Storage Temperature	$T_{STG}$	-65 to +200	°C

## ELECTRICAL CHARACTERISTICS

characteristics specified at  $T_A = 25^\circ\text{C}$ 

## Off Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Collector-Emitter Breakdown Voltage	$V_{(\text{BR})\text{CEO}}$	$I_C = 100 \mu\text{A}$	60			Volts
Collector-Base Cutoff Current	$I_{\text{CBO}1}$ $I_{\text{CBO}2}$ $I_{\text{CBO}3}$	$V_{\text{CB}} = 60 \text{ Volts}$ $V_{\text{CB}} = 50 \text{ Volts}$ $V_{\text{CB}} = 50 \text{ Volts}, T_A = 150^\circ\text{C}$			10 10 10	$\mu\text{A}$ nA $\mu\text{A}$
Emitter-Base Cutoff Current	$I_{\text{EBO}1}$ $I_{\text{EBO}2}$	$V_{\text{EB}} = 5 \text{ Volts}$ $V_{\text{EB}} = 4 \text{ Volts}$			10 10	$\mu\text{A}$ nA

## On Characteristics

Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
DC Current Gain	$h_{\text{FE}2}$	$I_C = 10 \mu\text{A}, V_{\text{CE}} = 5 \text{ Volts}$	100			
	$h_{\text{FE}3}$	$I_C = 100 \mu\text{A}, V_{\text{CE}} = 5 \text{ Volts}$	150		450	
	$h_{\text{FE}4}$	$I_C = 1 \text{ mA}, V_{\text{CE}} = 5 \text{ Volts}$	150		450	
	$h_{\text{FE}5}$	$I_C = 10 \text{ mA}, V_{\text{CE}} = 5 \text{ Volts}$	125			
	$h_{\text{FE}6}$	$I_C = 100 \mu\text{A}, V_{\text{CE}} = 5 \text{ Volts}$ $T_A = -55^\circ\text{C}$	60			
	$h_{\text{FE}3-1}/h_{\text{FE}3-2}$	$I_C = 100 \mu\text{A}, V_{\text{CE}} = 5 \text{ Volts}$	0.9		1.0	
Base-Emitter Voltage	$V_{\text{BE}}$	$V_{\text{CE}} = 5 \text{ Volts}, I_C = 100 \mu\text{A}$			0.7	Volts
	$ V_{\text{BE}1}-V_{\text{BE}2 1}$	$V_{\text{CE}} = 5 \text{ Volts}, I_C = 10 \mu\text{A}$			5	mVolts
	$ V_{\text{BE}1}-V_{\text{BE}2 2}$	$V_{\text{CE}} = 5 \text{ Volts}, I_C = 100 \mu\text{A}$			3	mVolts
	$ V_{\text{BE}1}-V_{\text{BE}2 3}$	$V_{\text{CE}} = 5 \text{ Volts}, I_C = 10 \text{ mA}$			5	mVolts
Base-Emitter Saturation Voltage	$V_{\text{BEsat}1}$	$I_C = 100 \mu\text{A}, I_B = 10 \mu\text{A}$			0.7	Volts
	$V_{\text{BEsat}2}$	$I_C = 1 \text{ mA}, I_B = 100 \mu\text{A}$			0.8	
Collector-Emitter Saturation Voltage	$V_{\text{CESat}1}$	$I_C = 100 \mu\text{A}, I_B = 10 \mu\text{A}$			0.20	Volts
	$V_{\text{CESat}2}$	$I_C = 1 \text{ mA}, I_B = 100 \mu\text{A}$			0.25	

## Dynamic Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Magnitude – Common Emitter, Short Circuit Forward Current Transfer Ratio	$ h_{FE1} $	$V_{CE} = 5$ Volts, $I_C = 500 \mu A$ , $f = 30$ MHz	1			
	$ h_{FE2} $	$V_{CE} = 5$ Volts, $I_C = 1$ mA, $f = 100$ MHz	1		5	
Small Signal Short Circuit Forward Current Transfer Ratio	$h_{FE}$	$V_{CE} = 10$ Volts, $I_C = 1$ mA, $f = 1$ kHz	150		600	
Open Circuit Output Capacitance	$C_{OBO}$	$V_{CB} = 5$ Volts, $I_E = 0$ mA, 100 kHz < $f < 1$ MHz			5	pF
Open Circuit Input Capacitance	$C_{IBO}$	$V_{EB} = 0.5$ Volts, $I_C = 0$ mA, 100 kHz < $f < 1$ MHz			8	pF
Noise Figure	$NF_1$ $NF_2$ $NF_3$	$V_{CE} = 10$ Volts, $I_C = 100 \mu A$ , $R_g = 3 k\Omega$ $f = 100$ Hz			7 3 2.5	dB
Noise Figure (wideband)	NF	$V_{CE} = 10$ Volts, $I_C = 100 \mu A$ , $R_g = 3 k\Omega$ 10 Hz < $f < 15.7$ kHz			3.5	dB
Short Circuit Input Impedance	$h_{ie}$	$V_{CB} = 10V$ , $I_C = 1mA$ , $f = 1kHz$	3		30	k $\Omega$
Open Circuit Output Admittance	$h_{oe}$	$V_{CB} = 10V$ , $I_C = 1mA$ , $f = 1kHz$	5		60	$\mu\Omega$
Open Circuit reverse Voltage Transfer Ratio	$h_{re}$	$V_{CB} = 10V$ , $I_C = 100\mu A$ , $f = 1kHz$			$25 \times 10^{-4}$	